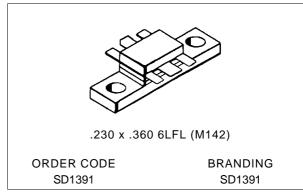


SD1391

RF & MICROWAVE TRANSISTORS UHF BASE STATION APPLICATIONS

PRELIMINARY DATA

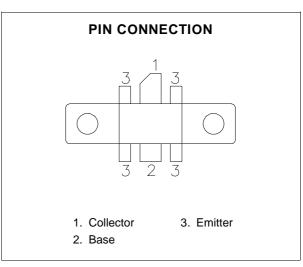
- 470 MHZ
- 24 VOLTS
- EFFICIENCY 50% MIN.
- Pout = 15 W WITH 11.0 dB MIN. GAIN
- CLASS AB
- COMMON EMITTER





The SD1391 is a gold metallized NPN planar transistor using diffused emitter ballast resistors for reliability and ruggedness.

The SD1391 is specifically designed as a low power, high gain driver and can be operated in Class A, B or C.



ABSOLUTE MAXIMUM RATINGS $(T_{case} = 25^{\circ}C)$

Symbol	Parameter	Value	Unit	
V _{CBO}	Collector-Base Voltage	48	V	
VCEO	Collector-Emitter Voltage	25	V	
V _{EBO} Emitter-Base Voltage		3.5	V	
Ic Collector Current		2.5	А	
P _{DISS} Power Dissipation (+25°C)		29	W	
T _J Junction Temperature		+200	°C	
T _{STG}	Storage Temperature	- 65 to +150	°C	

THERMAL DATA

R _{TH(j-c)} Junction-Case Thermal Resistance	6.0	°C/W
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ELECTRICAL SPECIFICATIONS (T_{case} = 25°C)

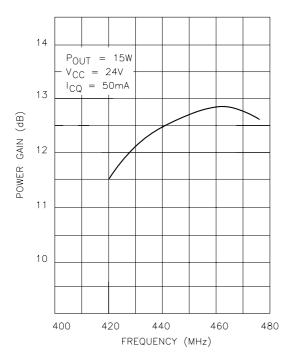
STATIC

Symbol	Test Conditions		Value			Unit	
Syllibol			Min.	Тур.	Max.	Onn	
BV _{CBO}	$I_C = 50 \text{ mA}$	$I_E = 0 \text{ mA}$		48	_	_	V
BV _{CEO}	$I_C = 20 \text{ mA}$	$I_B = 0 \text{ mA}$		25	_	_	V
BV_{EBO}	$I_E = 5 \text{ mA}$	$I_C = 0 \text{ mA}$		3.5	_	_	V
I _{CBO}	V _{CB} = 24 V	$I_E = 0 \text{ mA}$		_	_	1.0	mA
hfE	V _{CE} = 10 V	$I_C = 0.1 A$		10	_	100	

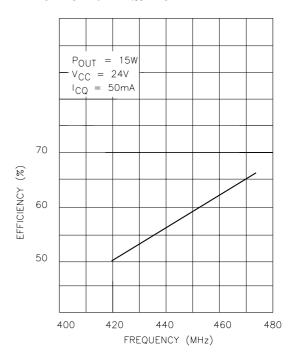
DYNAMIC

Symbol	Symbol Test Conditions			Value		Unit		
Syllibol				Min.	Тур.	Max.	Offic	
Pout	f = 470 MHz	$P_{IN} = 6.3 W$	$V_{CC} = 24V$	$I_{CQ} = 50 \text{ mA}$	15		1	W
ηс	f = 470 MHz	$P_{IN} = 6.3 W$	$V_{CC} = 24V$	$I_{CQ} = 50 \text{ mA}$	50	60		%
R _{TL}	f = 470 MHz	$P_{IN} = 6.3 \text{ W}$	$V_{CC} = 24V$	$I_{CQ} = 50 \text{ mA}$	10	_		dB
Сов	f = 1 MHz	$V_{CB} = 24 V$			_	_	24	pF

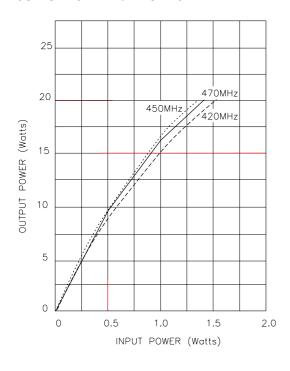
POWER GAIN vs FREQUENCY



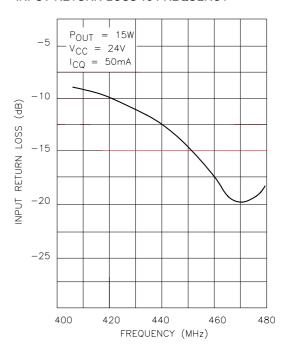
EFFICIENCY vs FREQUENCY



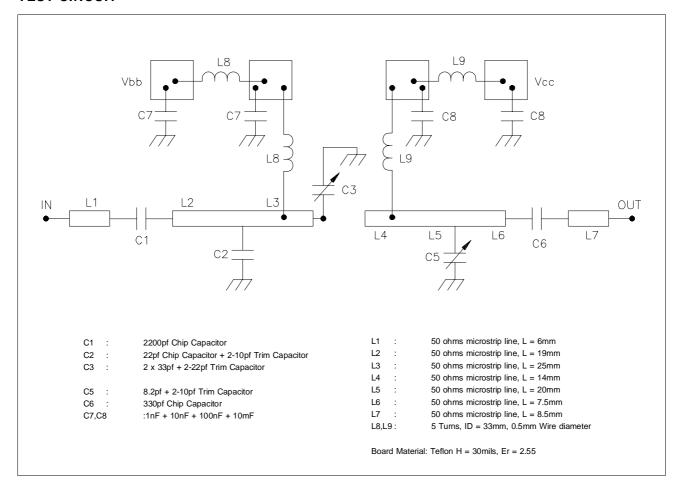
OUTPUT POWER vs INPUT POWER



INPUT RETURN LOSS vs FREQUENCY

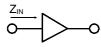


TEST CIRCUIT

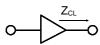


IMPEDANCE DATA





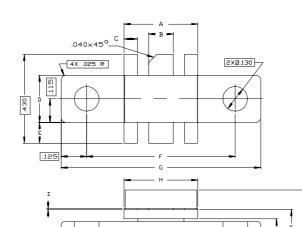
TYPICAL COLLECTOR LOAD IMPEDANCE



FREQ.	$Z_{IN}(\Omega)$	$Z_CL(\Omega)$
420 MHz	4.0 + j 2.2	7.2 + j 1.0
450 MHz	5.4 + j 3.9	6.8 + j 3.0
470 MHz	4.9 + j 5.7	6.6 + j 4.3

PACKAGE MECHANICAL DATA

Ref.: Dwg. No. 12-0142 rev. C UDCS No. 1010968



SG	SGS-THOMSON MICROELECTRONICS			CONT'D		
	MINIMUM Inches/mm	MAXIMUM Inches/mm		MINIMUM Inches/mm	MAXIMUM Inches/mm	
Α	.355/9,02	.365/9,27	К	.160/4,06	.180/4,57	
В	.115/2,92	.125/3,18	L	.230/5,84	.260/6,60	
С	.075/1,91	.085/2,16				
D	.225/5,72	.235/5,97				
Ε	.090/2,29	.110/2,79				
F	.720/18,29	.730/18,54				
G	.970/24,64	.980/24,89				
н	.355/9,02	.365/9,27				
Ι	.004/0,10	.006/0,15				
J	.120/3,05	.130/3,30				

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